

PHOTOCOUPLER
PS2521-1,-2,-4,PS2521L-1,-2,-4**LARGE FORWARD INPUT TYPE
HIGH ISOLATION VOLTAGE
MULTI PHOTOCOUPLER SERIES**

–NEPOC™ Series–

DESCRIPTION

The PS2521-1, -2, -4 and PS2521L-1, -2, -4 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor.

The PS2521-1, -2, -4 are in a plastic DIP (Dual In-line Package) and the PS2521L-1, -2, -4 are lead bending type (Gull-wing) for surface mount.

FEATURES

- Large forward input current ($I_F = 150 \text{ mA}$)
- High Isolation voltage ($BV = 5\,000 \text{ Vr.m.s.}$)
- High collector to emitter voltage ($V_{CEO} = 80 \text{ V}$)
- High-speed switching ($t_r = 3 \mu\text{s TYP.}$, $t_f = 5 \mu\text{s TYP.}$)
- Ordering number of taping product: PS2521L-1-E3, E4, F3, F4, PS2521L-2-E3, E4
- UL approved: File No. E72422 (S)

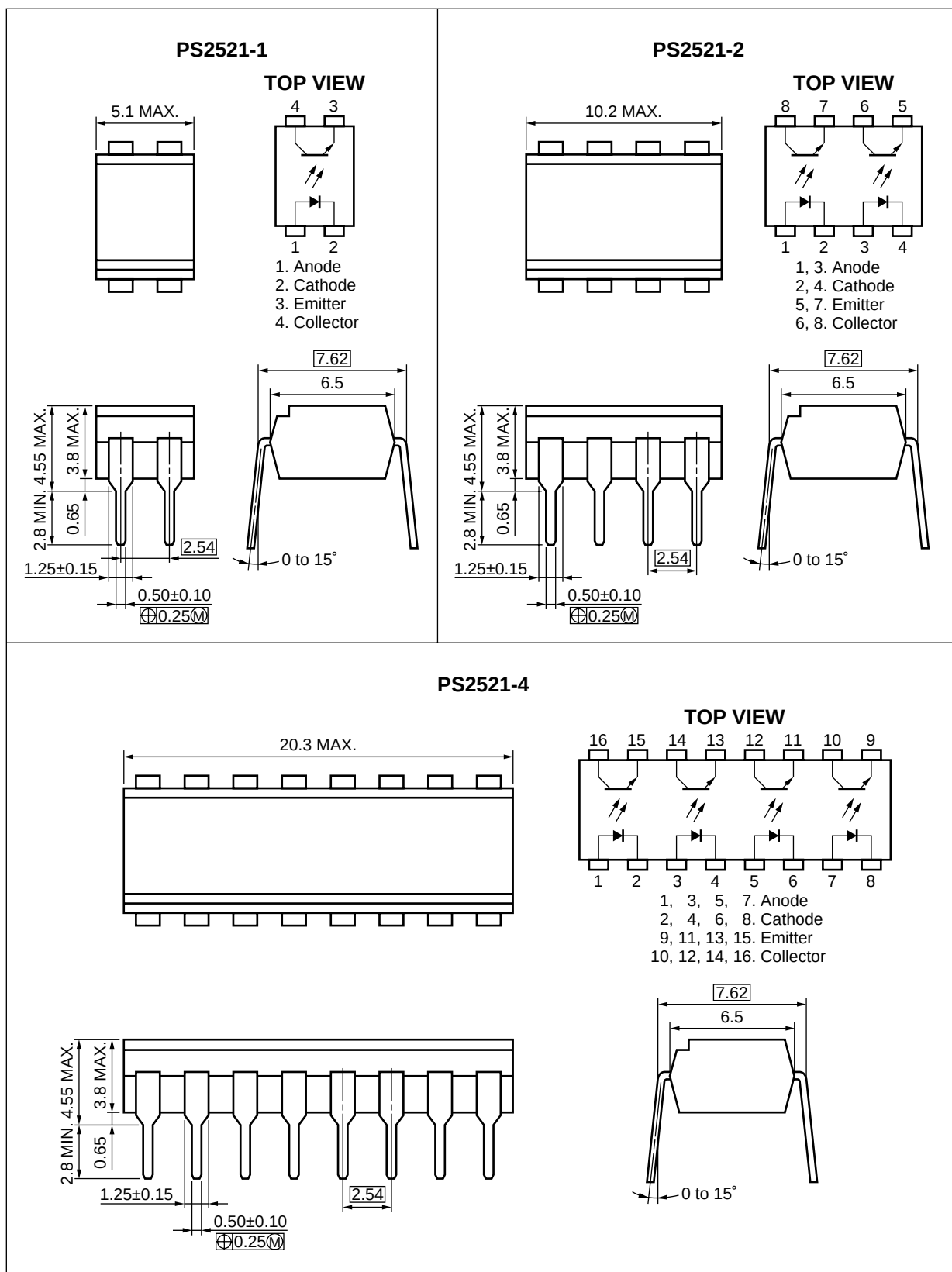
★ APPLICATIONS

- Exchange equipment
- FAX/MODEM
- LCR adapter

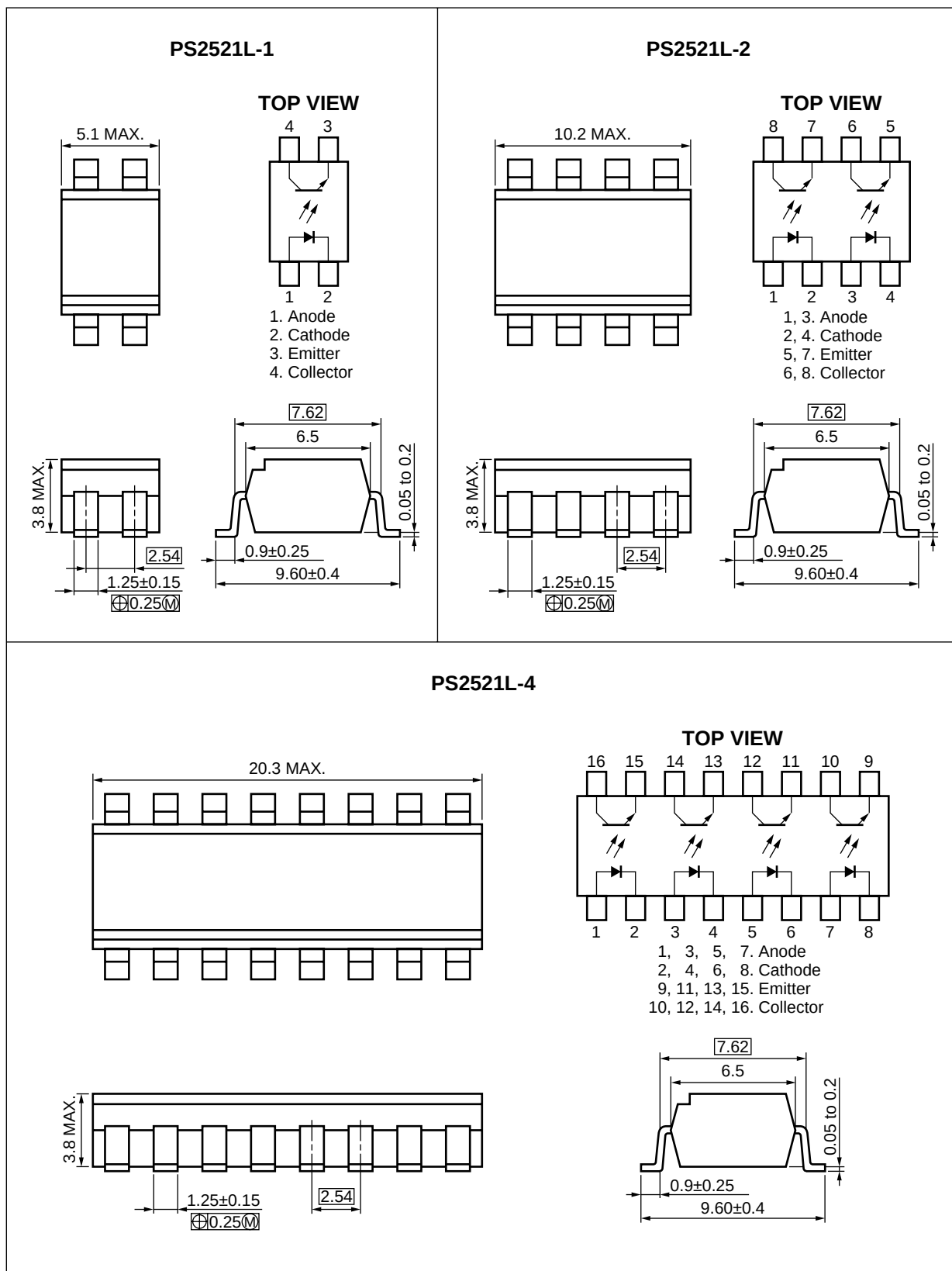
The information in this document is subject to change without notice.

★ PACKAGE DIMENSIONS (in millimeters)

DIP type



Lead bending type



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter		Symbol	Ratings		Unit
			PS2521-1, PS2521L-1	PS2521-2, -4, PS2521L-2, -4	
Diode	Forward Current (DC)	I_F	150		mA
	Reverse Voltage	V_R	6.0		V
	Power Dissipation Derating	$\Delta P_D/^{\circ}\text{C}$	2.5	2.0	mW/ $^{\circ}\text{C}$
	Power Dissipation	P_D	250	200	mW/ch
	Peak Forward Current ^{*1}	I_{FP}	1		A
Transistor	Collector to Emitter Voltage	V_{CEO}	80		V
	Emitter to Collector Voltage	V_{ECO}	6		V
	Collector Current	I_C	50		mA/ch
	Power Dissipation Derating	$\Delta P_C/^{\circ}\text{C}$	1.5	1.2	mW/ $^{\circ}\text{C}$
	Power Dissipation	P_C	150	120	mW/ch
Isolation Voltage ^{*2}		BV	5 000		Vr.m.s.
Operating Ambient Temperature		T_A	-55 to +100		$^{\circ}\text{C}$
Storage Temperature		T_{stg}	-55 to +150		$^{\circ}\text{C}$

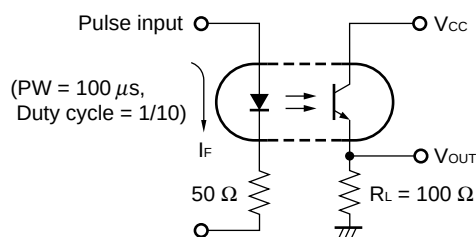
***1** PW = 100 μs , Duty Cycle = 1 %

***2** AC voltage for 1 minute at $T_A = 25\text{ }^{\circ}\text{C}$, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$)

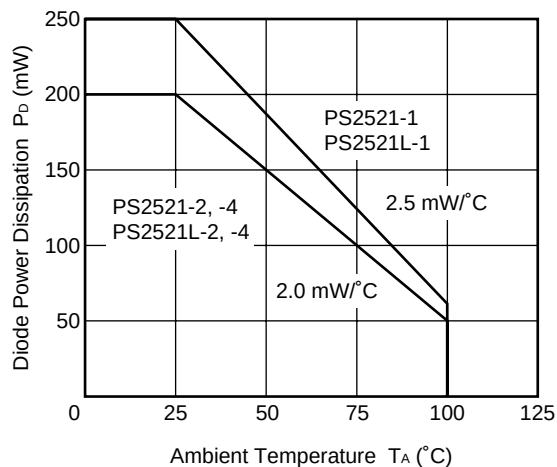
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V_F	$I_F = 100\text{ mA}$		1.3	1.7	V
	Reverse Current	I_R	$V_R = 5\text{ V}$			5	μA
	Terminal Capacitance	C_t	$V = 0\text{ V}$, $f = 1.0\text{ MHz}$		70		pF
Transistor	Collector to Emitter Dark Current	I_{CEO}	$V_{CE} = 80\text{ V}$, $I_F = 0\text{ mA}$			100	nA
Coupled	Current Transfer Ratio	CTR	$I_F = 100\text{ mA}$, $V_{CE} = 3\text{ V}$	20		80	%
	Collector Saturation Voltage	$V_{CE(sat)}$	$I_F = 100\text{ mA}$, $I_C = 4\text{ mA}$			0.3	V
	Isolation Resistance	R_{I-O}	$V_{I-O} = 1.0\text{ kV}_{DC}$	10^{11}			Ω
	Isolation Capacitance	C_{I-O}	$V = 0\text{ V}$, $f = 1.0\text{ MHz}$		0.6		pF
	Rise Time ^{*1}	t_r	$V_{CC} = 10\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$		3		μs
	Fall Time ^{*1}	t_f			5		

*1 Test circuit for switching time

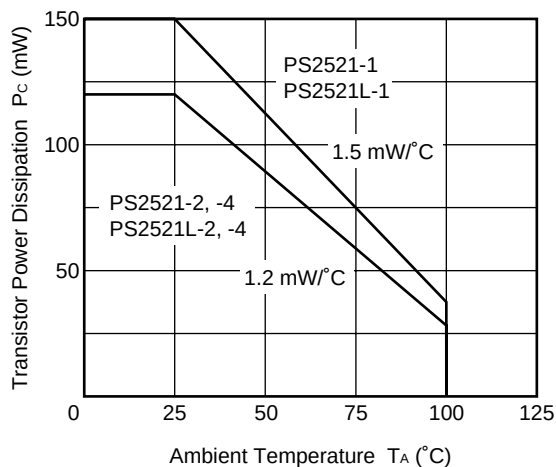


★ TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

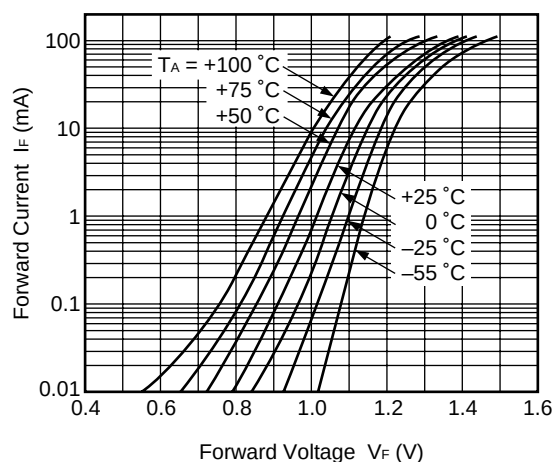
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



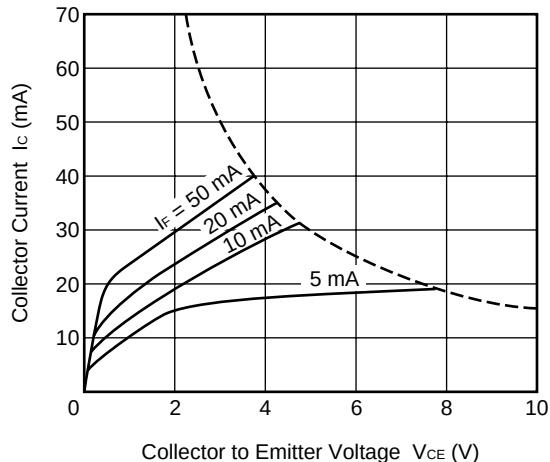
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



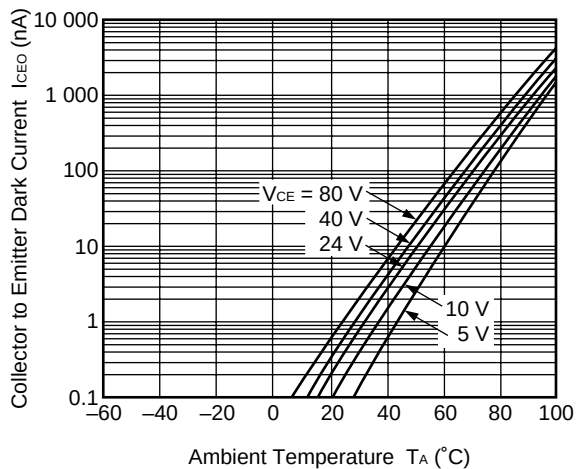
FORWARD CURRENT vs. FORWARD VOLTAGE



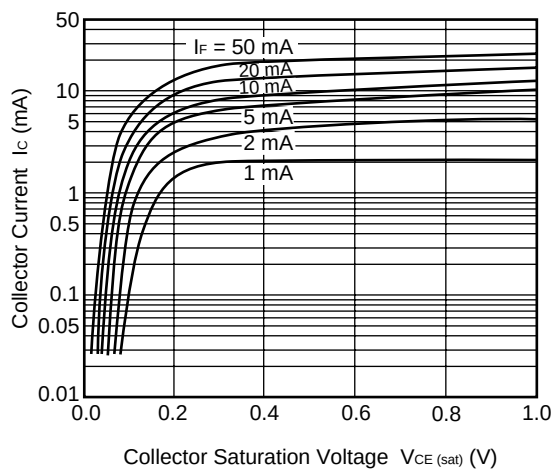
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



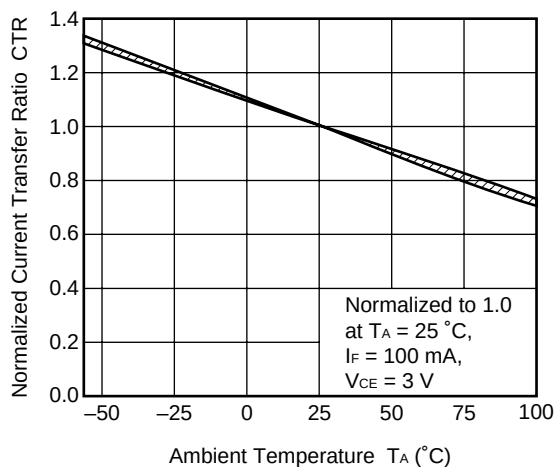
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



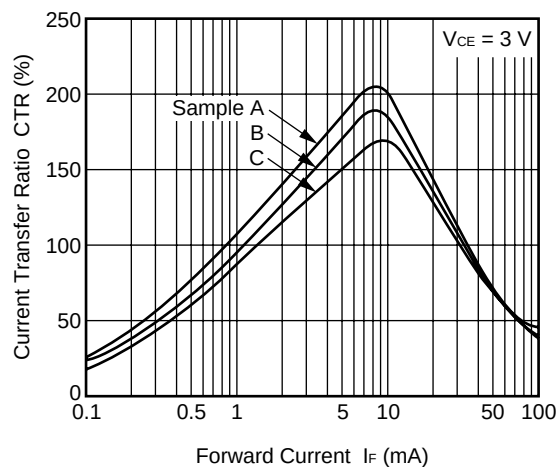
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



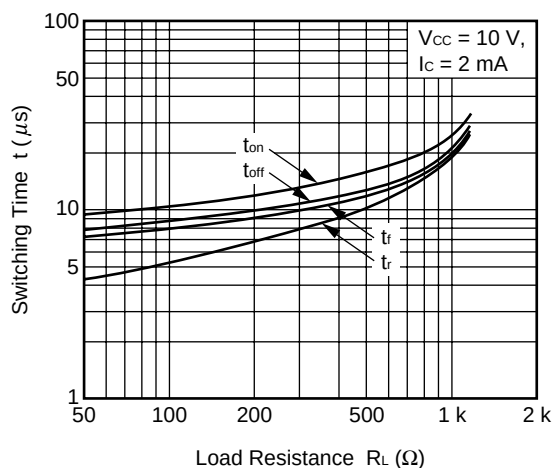
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



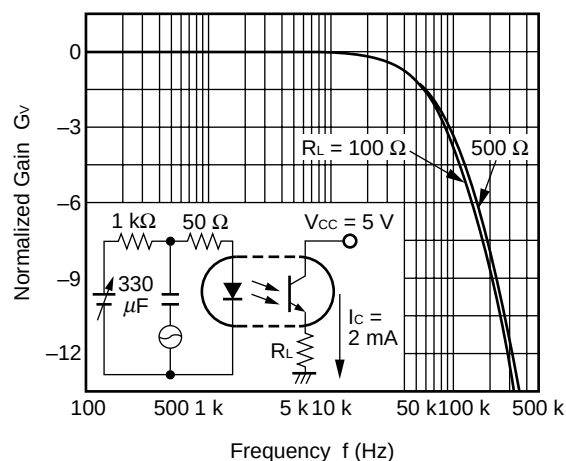
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



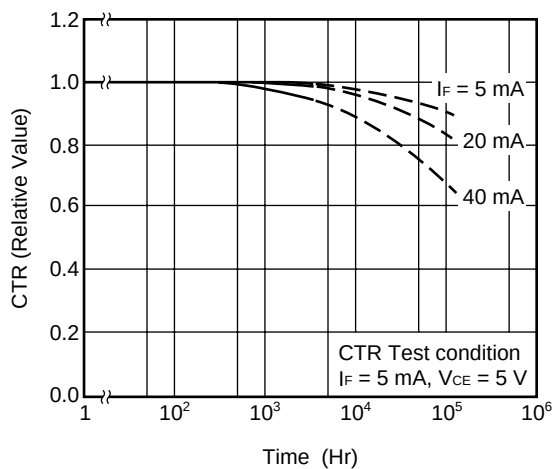
SWITCHING TIME vs. LOAD RESISTANCE



FREQUENCY RESPONSE



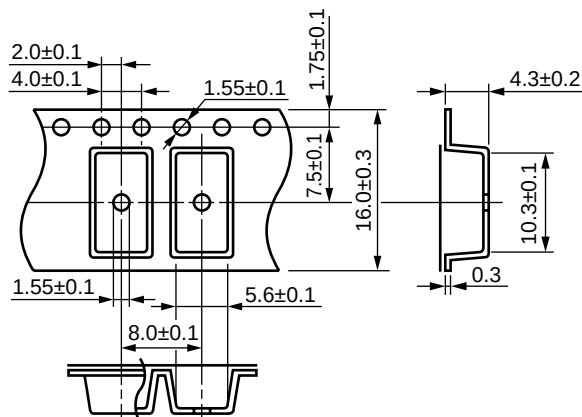
LONG TERM CTR DEGRADATION



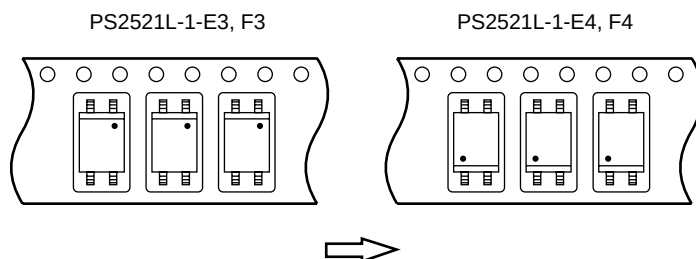
Remark The measurement of TYPICAL CHARACTERISTICS are only for reference, not guaranteed.

★ TAPING SPECIFICATIONS (in millimeters)

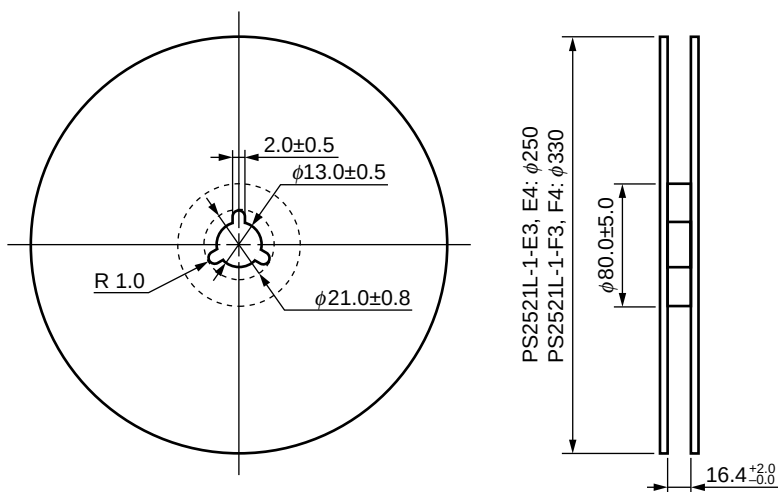
Outline and Dimensions (Tape)



Tape Direction

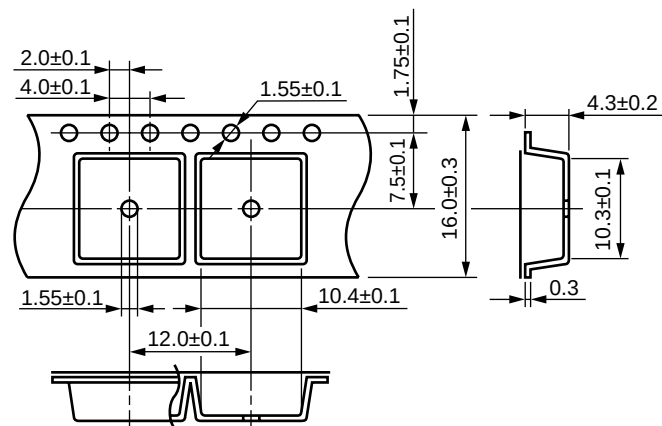


Outline and Dimensions (Reel)

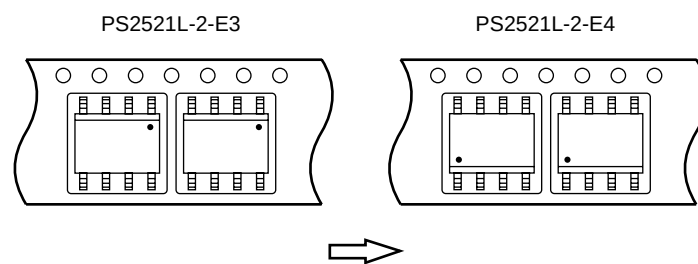


Packing: PS2521L-1-E3, E4 1 000 pcs/reel
PS2521L-1-F3, F4 2 000 pcs/reel

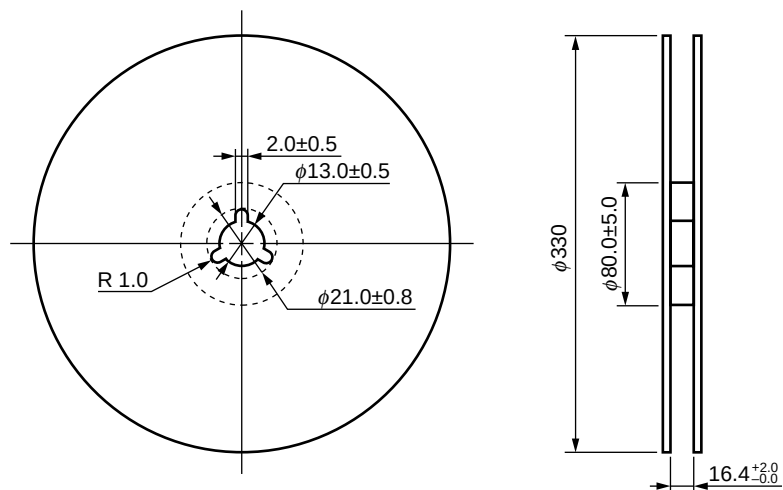
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



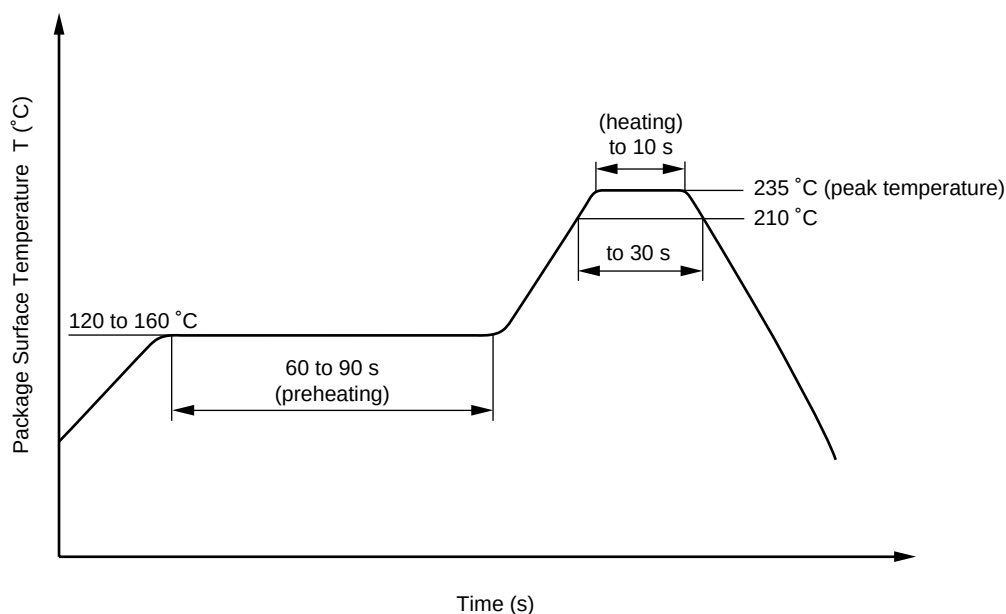
Packing: 1 000 pcs/reel

RECOMMENDED SOLDERING CONDITIONS

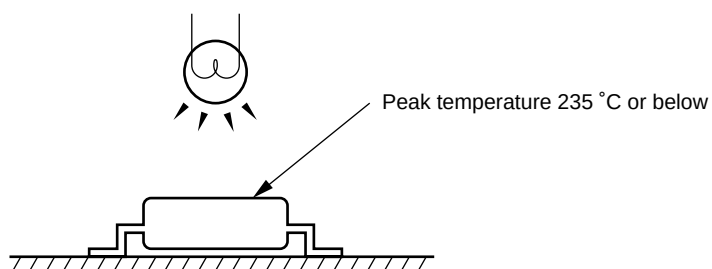
(1) Infrared reflow soldering

- Peak reflow temperature 235 °C (package surface temperature)
- Time of temperature higher than 210 °C 30 seconds or less
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



Caution Please avoid to removed the residual flux by water after the first reflow processes.



(2) Dip soldering

- Temperature 260 °C or below (molten solder temperature)
- Time 10 seconds or less
- Number of times One
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.